

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Jacson Liu Examiner: Guerrero,  
5 Maria F  
Filing Date: 11/03/1998 Art Unit: 2822  
Serial No.: 09/187,197 Docket No.: MVIP0005USA

10 Title: Shallow Trench Isolation Method for a  
Semiconductor Wafer

To: Commissioner for Patents  
P.O. BOX 1450  
15 Alexandria, VA 22313-1450

Subject: Reply to the Office action dated 04/23/2003

20 Dear Sir/Madam:

**AMENDMENTS**

25 In response to the Office action identified above,  
please amend the above-identified application as  
follows:

**In the specification:**

- 30 1. On page 6, lines 20-31, and page 7, lines 1-15, please  
replace the paragraph with the following:

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Also, because of different degrees of exposure (the

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